PC1231xNSZ1B Series

DIP 4pin Reinforced Insulation Type, High CMR, Low Input Current Photocoupler



Description

PC1231xNSZ1B Series contains an IRED optically coupled to a phototransistor.

It is packaged in a 4-pin DIP, available in wide-lead spacing option.

Input-output isolation voltage(rms) is 5kV.

CTR is 50% to 400% (at I_F=0.5mA,V_{CE}=5V,Ta=25 $^{\circ}\!C$)

Features

- 1. 4-pin DIP package
- 2. Double transfer mold package (Ideal for Flow Soldering)
- 3. Low input current type (I_F=0.5 mA)
- High noise immunity due to high common mode rejection voltage (CMR : MIN.10kV/µs)
- 5. Reinforced insulation type (Isolation distance : MIN. 0.4mm)
- Long creepage distance type (wide lead-form type only : MIN. 8mm)
- High isolation voltage between input and output (V_{iso}(rms): 5.0kV)
- 8. RoHS directive compliant

- Agency approvals/Compliance
- 1. Recognized by UL1577 (Double protection isolation), file No. E64380 (as model No. PC1231)
- 2. Approved by BSI, BS-EN62368-1 (as model No. **PC1231**)
- 3. Approved by SEMKO, EN60065, EN60335-1, EN60950 (as model No. **PC1231**)
- 4. Approved by DEMKO, EN60065, EN60335-1,EN60950, (as model No. **PC1231**)
- 5. Approved by NEMKO, EN60065,EN60335-1, EN60950 (as model No. **PC1231**)
- Approved by FIMKO, EN60065, EN60335-1, EN60950, (as model No. PC1231)
- 7. Recognized by CSA file No. CA95323 (as model No. **PC1231**)
- 8. Approved by VDE, DIN EN60747-5-5(*) (as an option) File No. 40008087 (as model No. **PC1231**)
- 9. Package resin : UL flammability grade (94V 0)

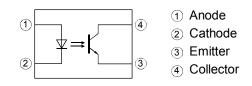
(*) DIN EN60747-5-5 : successor standard of DIN VDE0884.

Applications

- 1. Primary to secondary isolation in switch mode power supply
- 2. Noise suppression in switching circuits
- 3. Signal transmission between circuits of different potentials and impedances
- 4. Over voltage detection

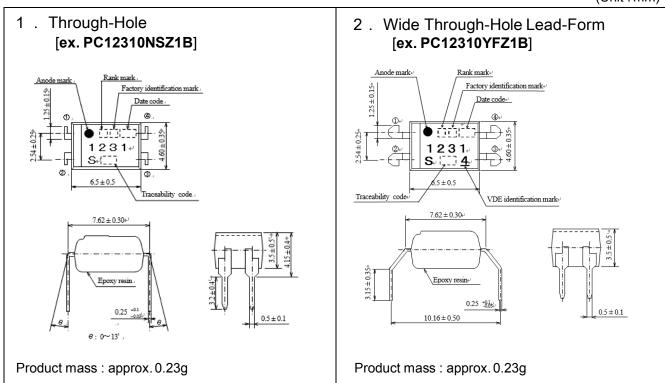


Internal Connection Diagram



Outline Dimensions

(Unit : mm)





Date code indication (Ex.)

3-digit number shall be marked the age indication of 1-digit number, and week code of 2-digit number. Week code "01" indicate the week including the first Thursday of January. And later, Monday is the starting point.

Year Week	
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Date code	MON	TUE	WED	THU	FRI	SAT	SUN
652	12/26	12/27	12/28	12/29	12/30	12/31	1/1
701	1/2	1/3	1/4	1/5	1/6	1/7	1/8
702	1/9	1/10	1/11	1/12	1/13	1/14	1/15
703	1/16	1/17	1/18	1/19	1/20	1/21	1/22
•	•	•	•	•	•	•	
	•	•	•	•	•	•	•
•	-	•		•	•		•
752	12/11	12/12	12/13	12/14	12/15	12/16	12/17
751	12/18	12/19	12/20	12/21	12/22	12/23	12/24
752	12/25	12/26	12/27	12/28	12/29	12/30	12/31
801	1/1	1/2	1/3	1/4	1/5	1/6	1/7

Factory identification mark and Plating material

Factory identification Mark	Country of origin	Plating material		
К	Japan	SnBi (Bi : 1~4%)		

Rank mark

Refer to the Model Line-up table.

Absolute Maximum Ratings

		$(T_a=25^{\circ}C)$		
	Parameter	Symbol	Rating	Unit
	Forward current	I _F	10	mA
T ,	*1 Peak forward current	I _{FM}	200	mA
Input	Reverse voltage	V _R	6	V
	Power dissipation	Р	15	mW
Output	Collector-emitter voltage	V _{CEO}	80	V
	Emitter-collector voltage	V _{ECO}	6	V
	Collector current	I _C	50	mA
	Collector power dissipation	P _C	150	mW
Total p	ower dissipation	P _{tot}	170	mW
*2 Isolation voltage		V _{iso} (rms)	5	kV
Operating temperature		T _{opr}	-30 to $+100$	C
Storage temperature		T _{stg}	-55 to +125	C
*2 Solder	ing temperature	T _{sol}	270	°C

*1 Pulse width \leq 100 µs, Duty ratio :0.001 *2 40 to 60% RH, AC for 1 minute *3 For 10s

Electro-optical Characteristics

(Ta=25°C)

Parameter			Symbol	Condition	MIN.	TYP.	MAX.	Unit
Forward voltage		V _F	I _F =5mA	-	1.2	1.4	V	
Input	Reverse current	Reverse current		$V_R=4V$	_	_	10	μΑ
	Terminal capacitance		Ct	V=0, f=1kHz	_	30	250	pF
	Dark current		I _{CEO}	$V_{CE}=50V, I_{F}=0$	-	-	100	nA
Output Collector-emitter breakdown voltage		BV _{CEO}	$I_{C}=0.1mA, I_{F}=0$	80	_	_	V	
	Emitter-collector breakdown voltage		BV _{ECO}	$I_{E}=10\mu A, I_{F}=0$	6	_	-	V
	Collector current		I _C	$I_F=0.5mA, V_{CE}=5V$	0.25	-	2.0	mA
Collector-emitter saturation voltage		V _{CE(sat)}	$I_F=10mA$, $I_C=1mA$	_	-	0.2	V	
Transfer	Transfer Isolation resistance		R _{ISO}	DC500V, 40 to 60%RH	5×10 ¹⁰	1×10 ¹¹	-	Ω
charac-	Floating capacitance		C _f	V=0, f=1MHz	_	0.6	1.0	pF
teristics	Response time	Risetime	tr	$V_{CE}=2V, I_{C}=2mA, R_{L}=100\Omega$	_	4	18	μs
		Falltime	t _f		-	3	18	μs
Common mode rejection ratio		CMR	$Ta=25^{\circ}C, R_{L}=470\Omega$ $V_{CM}=1.5kV(peak),$ $I_{F}=0, Vcc=9V, Vnp=100mV$	10	_	_	kV/μs	

SHARP

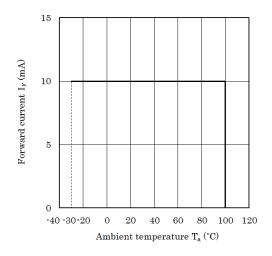
Model Line-up

Lead Form	Through-Hole		I _C [mA] (I _F =0.5mA,
	Sleeve	leeve Rank mark	
Package	100pcs/sleeve		V _{CE} =5V, T _a =25°C)
	PC12310NSZ1B	with or "_"	0.25 ~ 2
Model No.	PC12311NSZ1B	A	0.5 ~ 1.25

Lead Form	Wide Through-Hole		I _C [mA]
	Sleeve	Rank mark	(I _F =0.5mA, V _{CE} =5V,
Package	100pcs/sleeve		v _{CE} −5v, T _a =25°C)
	PC12310YFZ1B	with or "_"	0.25 ~ 2
Model No.	PC12311YFZ1B	A	0.5 ~ 1.25

Please contact a local SHARP sales representative to inquire about production status.

Fig.1 Forward Current vs. Ambient Temperature





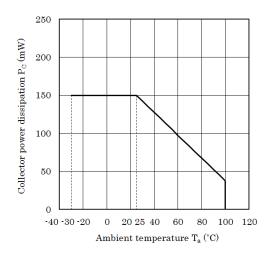


Fig.5 Peak Forward Current vs. Duty Ratio

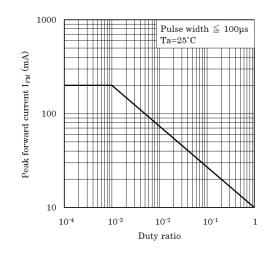
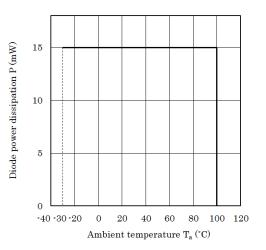


Fig.2 Diode Power Dissipation vs. Ambient Temperature





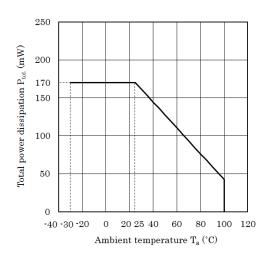


Fig.6 Forward Current vs. Forward Voltage

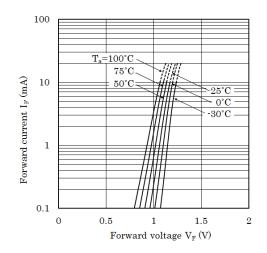
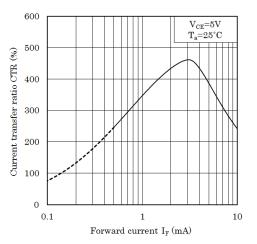


Fig.7 Current Transfer Ratio vs. Forward Current





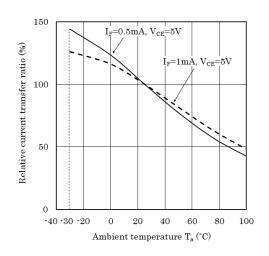


Fig.11 Collector Dark Current vs. Ambient Temperature

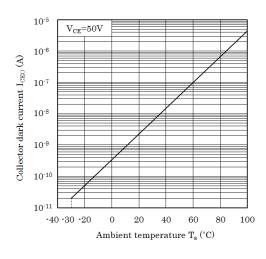


Fig.8 Collector Current vs. Collector-emitter Voltage

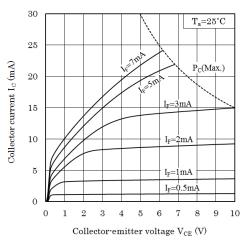
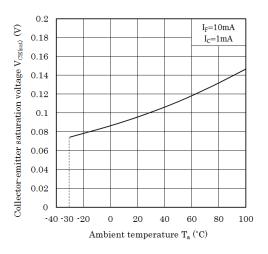


Fig.10 Collector - emitter Saturation Voltage vs. Ambient Temperature





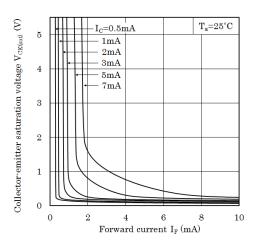




Fig.13 Response Time vs. Load Resistance

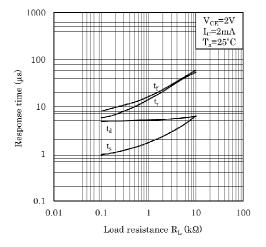


Fig.14 Test Circuit for Response Time

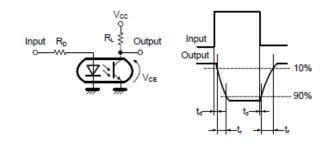
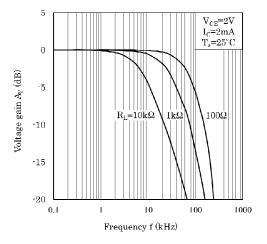


Fig.16 Test Circuit for Frequency Response





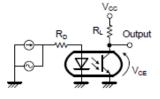
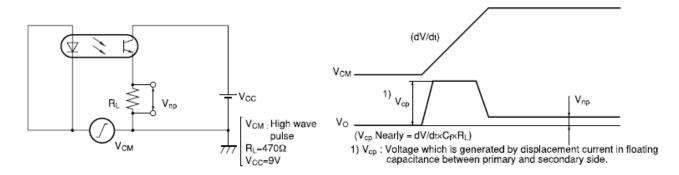


Fig.17 Test Circuit for Common Mode Rejection Voltage



Remarks : Please be aware that all data in the graph are just for reference and not for guarantee.



Design Considerations

• Design guide

While operating at I_F <0.5mA, CTR variation may increase. Please make design considering this fact.

In case that some sudden big noise caused by voltage variation is provided between primary and secondary terminals of photocoupler some current caused by it is floating capacitance may be generated and result in false operation since current may go through IRED or current may change. If the photocoupler may be used under the circumstances where noise will be generated we recommend to

use the bypass capacitors at the both ends of IRED.

This product is not designed against irradiation and incorporates non-coherent IRED.

• Degradation

In general, the emission of the IRED used in photocouplers will degrade over time. In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

☆ For additional design assistance, please review our corresponding Optoelectronic Application Notes.

Manufacturing Guidelines

• Soldering Method

Flow Soldering:

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 270°C and within 10s. Preheating is within the bounds of 100 to 150°C and 30 to 80s. Please don't solder more than twice.

Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C. Please don't solder more than twice

Other notice

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.

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• Cleaning instructions

Solvent cleaning:

Solvent temperature should be 45°C or below. Immersion time should be 3 minutes or less.

Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

Recommended solvent materials :

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol. In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

• Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this product.

Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBB and PBDE are not used in this product at all.

(1) The RoHS directive(2011/65/EU)

This product complies with the RoHS directive(2011/65/EU)

Object substances: mercury, lead, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE)

(2) Content of six substances specified in Management Methods for Control of Pollution Caused by Electronic Information Products Regulation (Chinese: 电子信息产品污染控制管理办法).

	Hazardous Substances						
Category	Lead (Pb)	Mercury (Hg)	Cadmium (Cd)	Hexavalent chromium (Cr ⁶⁺)	Polybrominated biphenyls (PBB)	Polybrominated diphenyl ethers (PBDE)	
Photocoupler	0	0	0	0	0	0	

This table is prepared in accordance with the provisions of SJ/T 11364.

• : Indicates that said hazardous substance contained in all of the homogeneous materials for this part is below the limit requirement of GB/T 26572.

Package specification

• Sleeve package Through-Hole

Package materials

Sleeve : HIPS/PS or PC (with anti-static material) Stopper : EPM

Package method

MAX. 100pcs. of products shall be packaged in a sleeve and both of sleeve edges shall be fixed by stoppers. MAX. 25 sleeves (Product : 2,500pcs.) above shall be packaged in inner case and sealed by tape . Max 2 bags(product : 5,000pcs) above shall be packaged in packing case , and put a cushioning material inside.

Sleeve outline dimensions

